

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSV)

# 2SK2967

DC-DC Converter, Relay Drive and Motor Drive Applications

Unit: mm

- Low drain-source ON resistance :  $R_{DS(ON)} = 48 \text{ m}\Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 30 \text{ S}$  (typ.)
- Low leakage current :  $I_{DSS} = 100 \text{ }\mu\text{A}$  (max) ( $V_{DS} = 250 \text{ V}$ )
- Enhancement mode :  $V_{th} = 1.5 \sim 3.5 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

## Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	250	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		$V_{DGR}$	250	V
Gate-source voltage		$V_{GSS}$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	30	A
	Pulse (Note 1)	$I_{DP}$	120	A
Drain power dissipation ( $T_c = 25^\circ\text{C}$ )		$P_D$	150	W
Single pulse avalanche energy (Note 2)		$E_{AS}$	925	mJ
Avalanche current		$I_{AR}$	30	A
Repetitive avalanche energy (Note 3)		$E_{AR}$	15	mJ
Channel temperature		$T_{ch}$	150	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	$-55 \sim 150$	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

## Thermal Characteristics

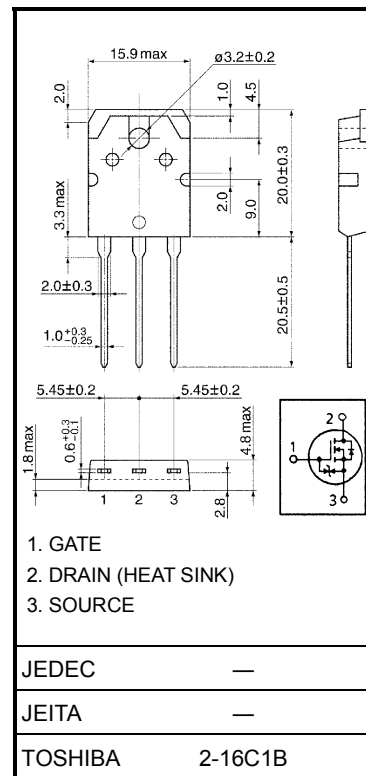
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	0.833	$^\circ\text{C} / \text{W}$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	50	$^\circ\text{C} / \text{W}$

Note 1: Ensure that the channel temperature does not exceed  $150^\circ\text{C}$ .

Note 2:  $V_{DD} = 50 \text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 1.74 \text{ mH}$ ,  $I_{AR} = 30 \text{ A}$ ,  $R_G = 25 \text{ }\Omega$

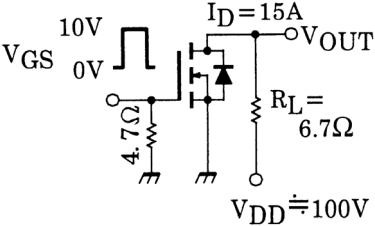
Note 3: Repetitive rating: pulse width limited by maximum channel temperature.

This transistor is an electrostatic-sensitive device.  
Please handle with caution.



Weight: 4.6 g (typ.)

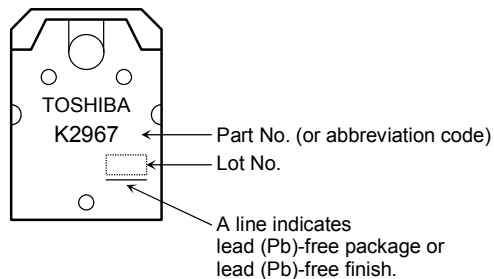
## Electrical Characteristics (Ta = 25°C)

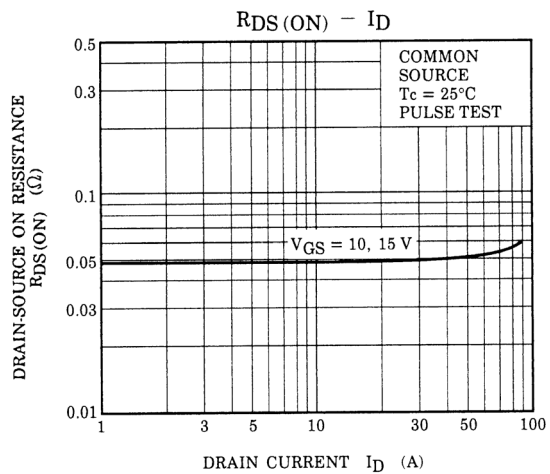
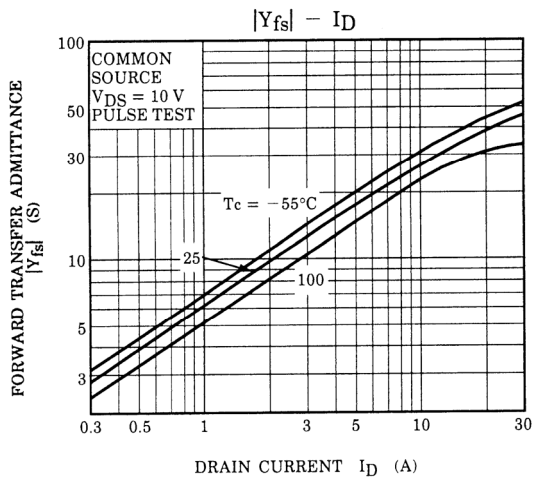
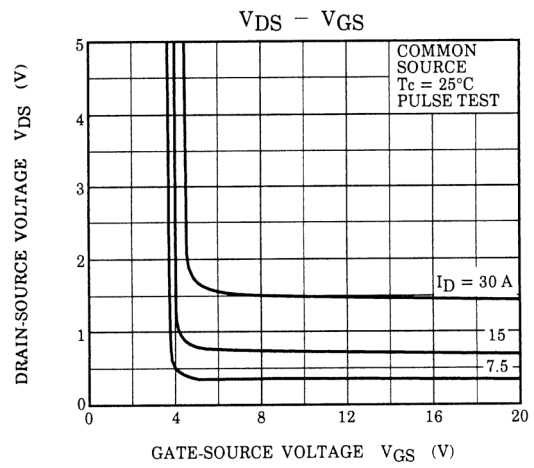
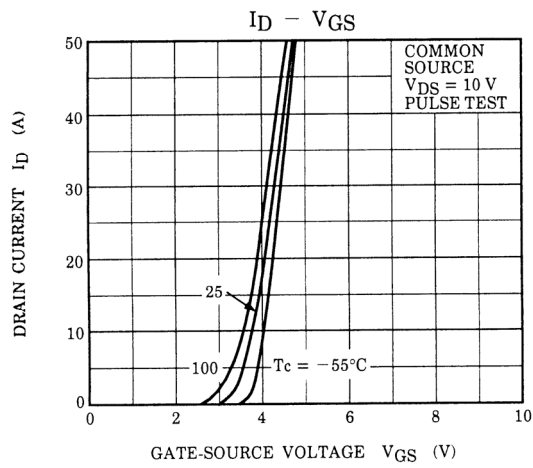
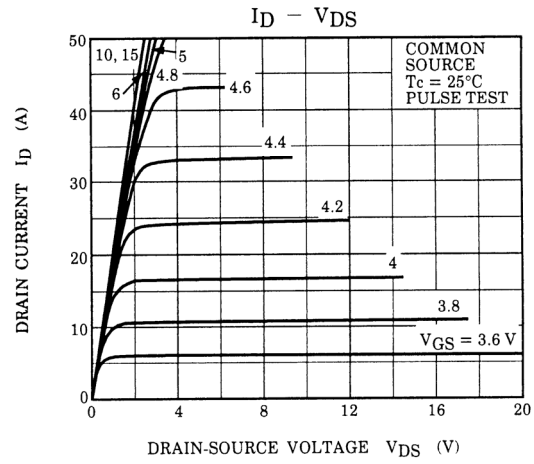
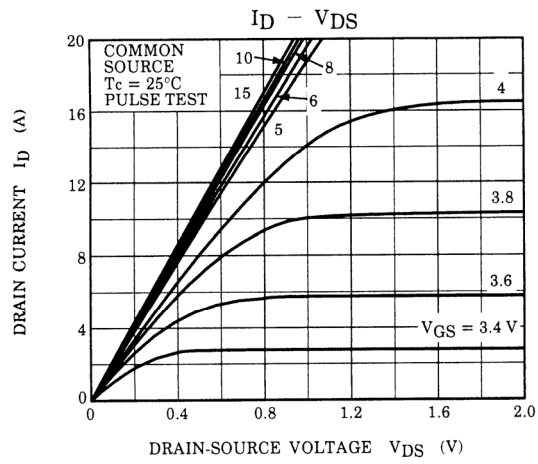
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-off current		$I_{DSS}$	$V_{DS} = 250 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR) DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	250	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	1.5	—	3.5	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$	—	48	68	$\text{m}\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 15 \text{ A}$	15	30	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	5400	—	pF
Reverse transfer capacitance		$C_{rss}$		—	580	—	
Output capacitance		$C_{oss}$		—	1900	—	
Switching time	Rise time	$t_r$	 <p><math>I_D = 15 \text{ A}</math> <math>R_L = 6.7 \Omega</math> <math>V_{DD} \approx 100 \text{ V}</math> Duty <math>\leq 1\%</math>, <math>t_w = 10 \mu\text{s}</math></p>	—	20	—	ns
	Turn-on time	$t_{on}$		—	50	—	
	Fall time	$t_f$		—	35	—	
	Turn-off time	$t_{off}$		—	200	—	
Total gate charge (gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 200 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	—	132	—	nC
Gate-source charge		$Q_{gs}$		—	80	—	
Gate-drain ("miller") Charge		$Q_{gd}$		—	52	—	

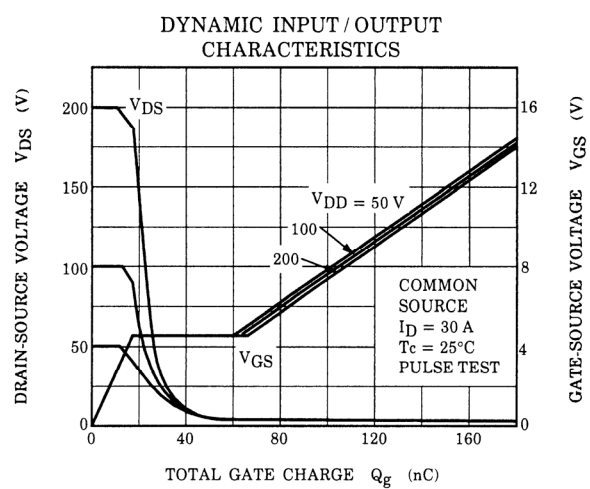
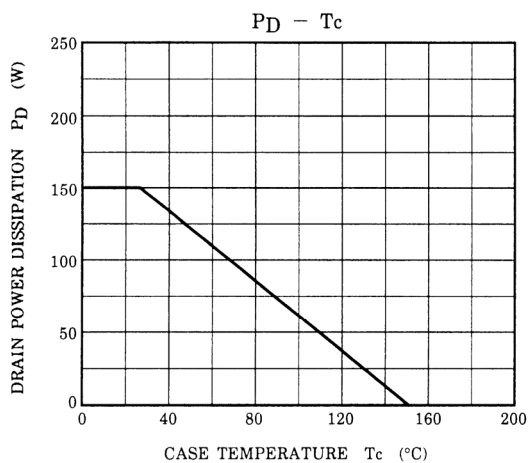
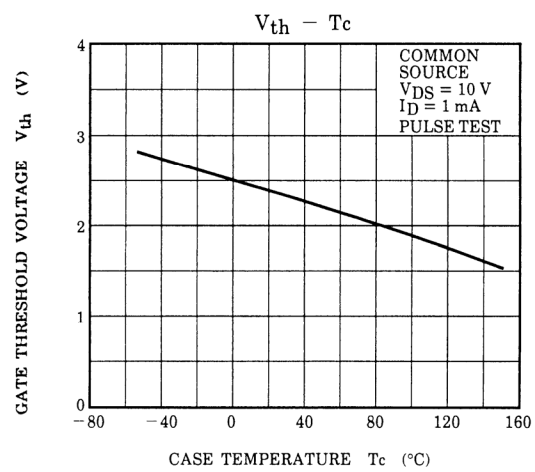
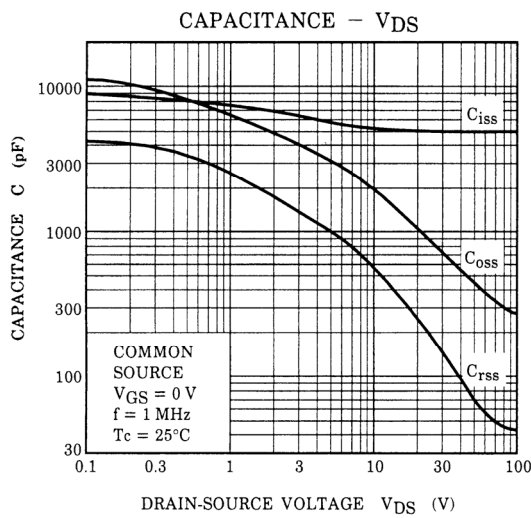
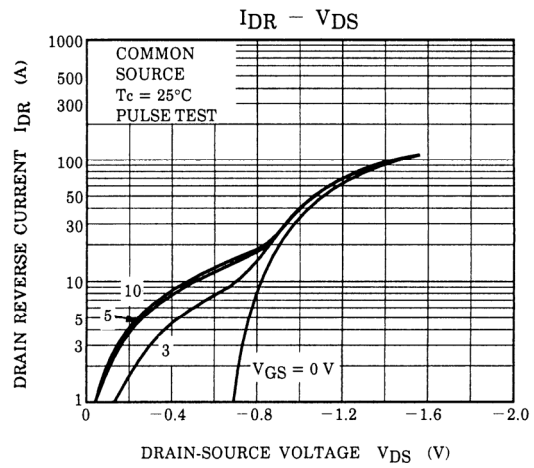
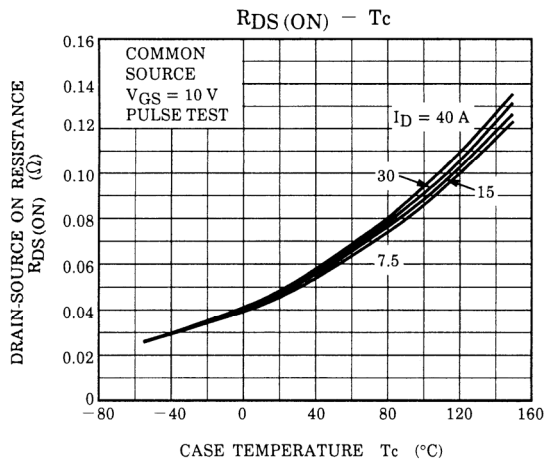
## Source-Drain Ratings and Characteristics (Ta = 25°C)

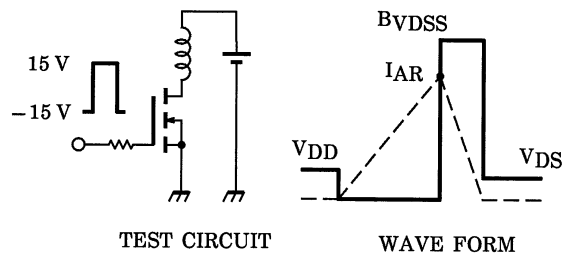
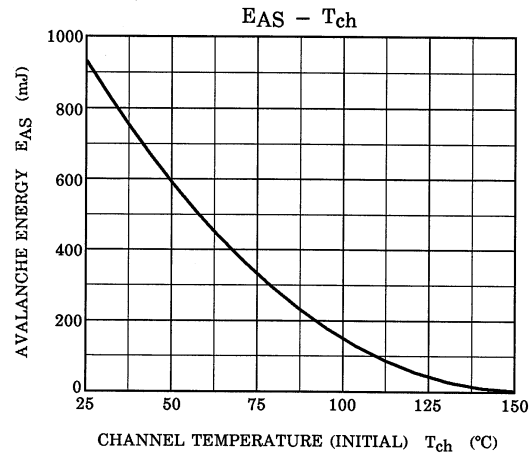
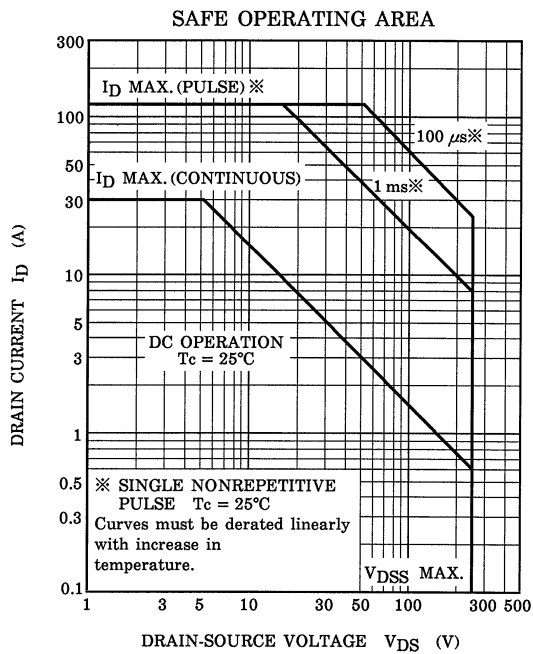
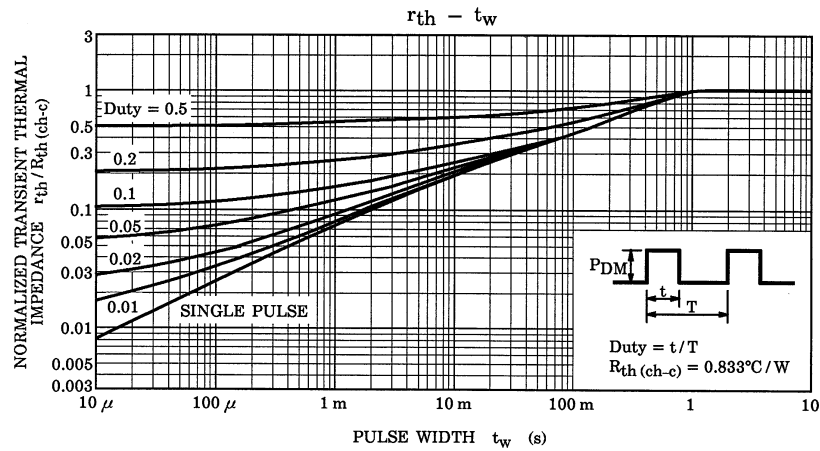
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	30	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	120	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = 30 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-2.0	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 30 \text{ A}, V_{GS} = 0 \text{ V}$	—	270	—	ns
Reverse recovery charge	$Q_{rr}$	$dI_{DR} / dt = 100 \text{ A} / \mu\text{s}$	—	3.0	—	$\mu\text{C}$

## Marking









$$R_G = 25 \, \Omega \quad V_{DD} = 50 \, \text{V}, L = 1.74 \, \text{mH} \quad E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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